Abstracts

Implementation of RF power MOS in 0.18/spl mu/m CMOS technology for single chip solution

Heng-Ming Hsu, Chih-Wei Chen, Jiong-Guang Su, Ta-Hsun Yeh, J.C.-H. Lin, J.Y.-C. Sun and Chun Hsiung Chen. "Implementation of RF power MOS in 0.18/spl mu/m CMOS technology for single chip solution." 2002 MTT-S International Microwave Symposium Digest 02.2 (2002 Vol. II [MWSYM]): 1027-1030 vol.2.

This paper presents a complete portfolio of silicon integrated RF power MOS using 0.18/spl mu/m CMOS technology in the first time. The proposed structure of power MOS promises high breakdown voltage, and presents excellent RF characteristics. To guarantee the production level, a complete qualification testing is also included.

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